

Technical Data Sheet

1.5mm Side Face Infrared LED

IR928C



Features

- High reliability
- High radiant intensity
- Peak wavelength $\lambda_p = 940\text{nm}$
- 2.54mm Lead spacing
- Low forward voltage
- Pb-Free
- This product itself will remain within RoHS compliant version.

Descriptions

- EVERCOLORS's Infrared Emitting Diode (IR-23C) is a high intensity diode , molded in a water clear plastic package.
- The miniature side- facing device has a chip , that emits radiation from the side of the clear package.

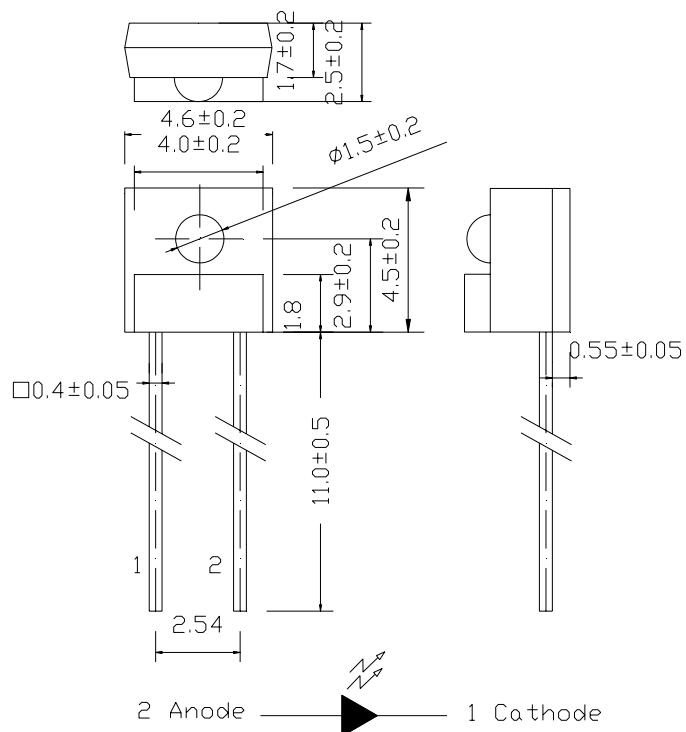
Applications

- Mouse
- Optoelectronic switch
- Infrared applied system

Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
IR-23C	GaAlAs	Water,Clear

Package Dimensions



Notes: 1. All dimensions are in millimeters

2. Tolerances unless dimensions $\pm 0.25\text{mm}$

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Units
Continuous Forward Current	I_F	50	mA
Peak Forward Current(*1)	I_{FP}	1.0	A
Reverse Voltage	V_R	5	V
Operating Temperature	T_{opr}	-25 ~ +85	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 ~ +85	$^\circ\text{C}$
Soldering Temperature(*2)	T_{sol}	260	$^\circ\text{C}$
Power Dissipation at(or below) 25°C Free Air Temperature	P_d	75	mW

Notes: *1: I_{FP} Conditions--Pulse Width $\leq 100\ \mu\text{s}$ and Duty $\leq 1\%$.

*2:Soldering time ≤ 5 seconds.

Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Light Current	I _{c(ON)}	I _F =4mA, V _{CE} =3.5V	265	--	1870	μA
Peak Wavelength	λ p	I _F =20mA	--	940	--	nm
Spectral Bandwidth	Δ λ	I _F =20mA	--	50	--	nm
Forward Voltage	V _F	I _F =20mA	--	1.2	1.5	V
Reverse Current	I _R	V _R =5V	--	--	10	μA
View Angle	2θ 1/2	I _F =20mA	--	40	--	deg

Wide Rank

Parameter	Symbol	Min	Max	Unit	Test Condition
5-2	I _{c(ON)}	1053	1870	μA	I _F =4mA, V _{CE} =3.5V
6-1	I _{c(ON)}	650	1274	μA	I _F =4mA, V _{CE} =3.5V
6-2	I _{c(ON)}	465	750	μA	I _F =4mA, V _{CE} =3.5V
7-1	I _{c(ON)}	347	550	μA	I _F =4mA, V _{CE} =3.5V
7-2	I _{c(ON)}	306	441	μA	I _F =4mA, V _{CE} =3.5V
7-3	I _{c(ON)}	265	358	μA	I _F =4mA, V _{CE} =3.5V

Typical Electro-Optical Characteristics Curves

Fig.1 Forward Current vs.
Ambient Temperature

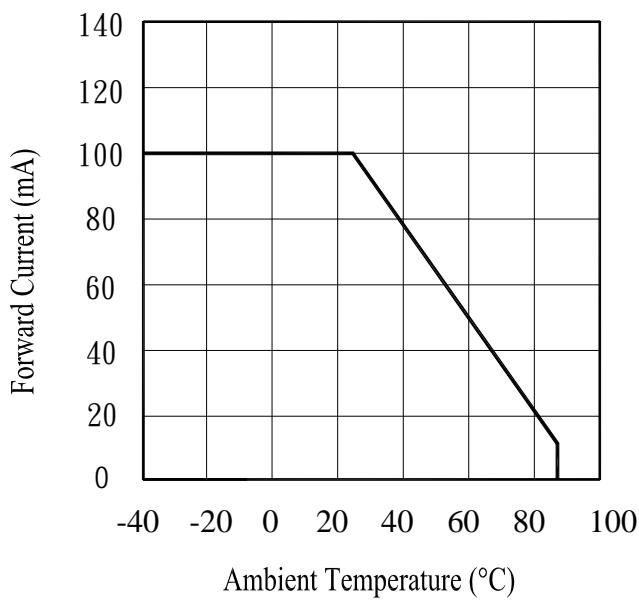


Fig.2 Spectral Distribution

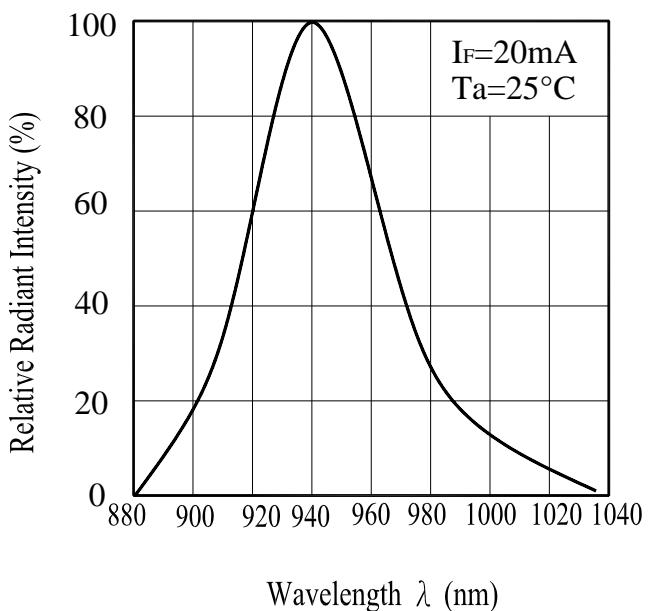


Fig.3 Peak Emission Wavelength
Ambient Temperature

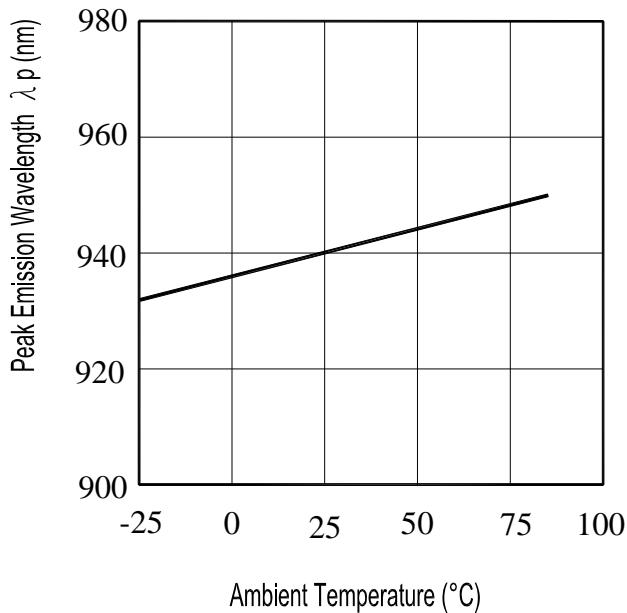
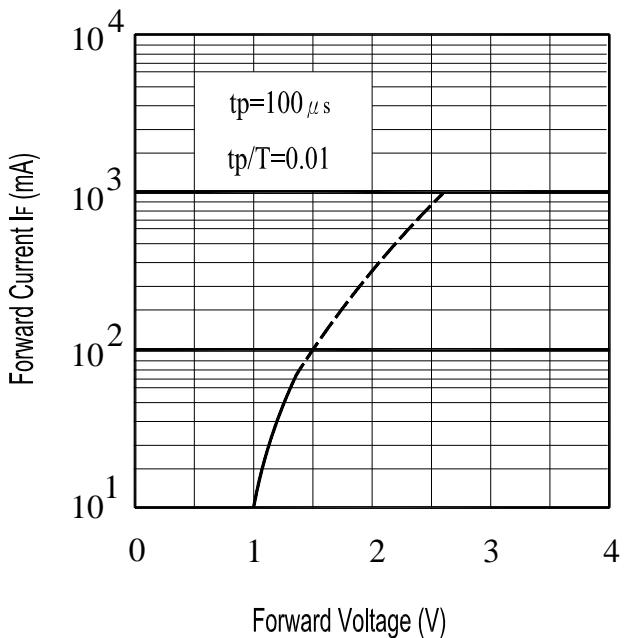


Fig.4 Forward Current
vs. Forward Voltage



Typical Electro-Optical Characteristics Curves

Fig.5 Forward Voltage vs.
Ambient Temperature

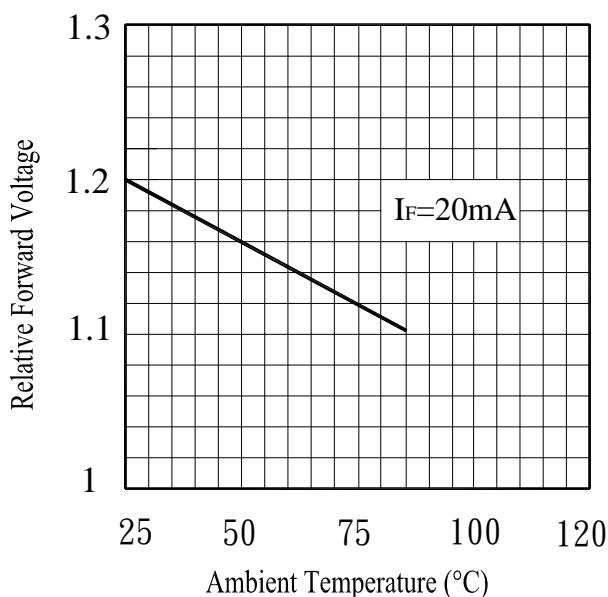
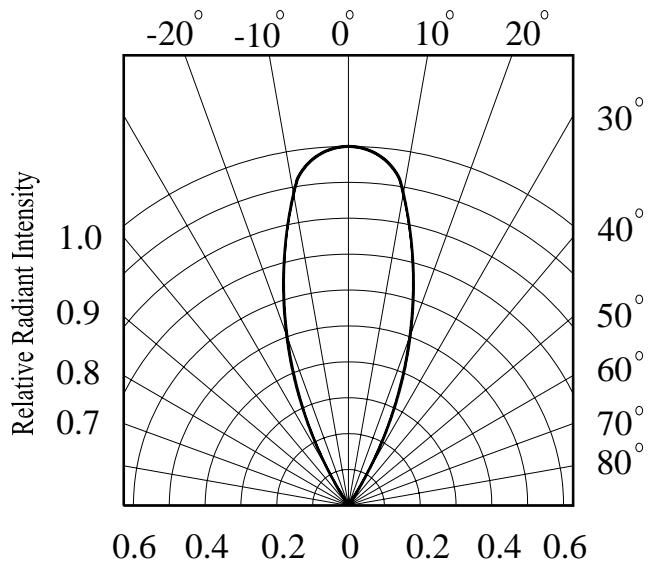


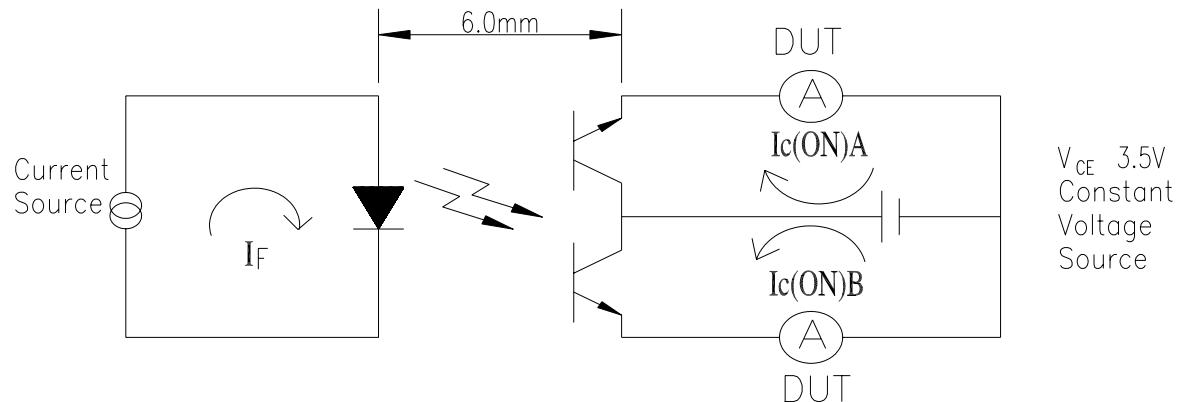
Fig.6 Relative Radiant Intensity vs.
Angular Displacement



■ Test Method For $I_{C(ON)}$:

Condition: $I_F=4\text{mA}$, $V_{CE}=3.5\text{V}$

The intensity testing method for infrared emitting diode



Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO.	Item	Test Conditions	Test Hours/ Cycles	Sample Sizes	Failure Judgement Criteria	Ac/Re
1	Solder Heat	TEMP. : $260^{\circ}\text{C} \pm 5^{\circ}\text{C}$	10secs	22pcs		0/1
2	Temperature Cycle	H : $+100^{\circ}\text{C}$ L : -40°C	15mins 5mins 15mins	300Cycles	22pcs	I _R \geq U $\times 2$ E _e \leq L $\times 0.8$ V _F \geq U $\times 1.2$
3	Thermal Shock	H : $+100^{\circ}\text{C}$ L : -10°C	5mins 10secs 5mins	300Cycles	22pcs	U : Upper Specification
4	High Temperature Storage	TEMP. : $+100^{\circ}\text{C}$	1000hrs	22pcs	Limit L : Lower Specification	0/1
5	Low Temperature Storage	TEMP. : -40°C	1000hrs	22pcs	Limit	0/1
6	DC Operating Life	I _F =20mA	1000hrs	22pcs		0/1
7	High Temperature/ High Humidity	85°C / 85% R.H	1000hrs	22pcs		0/1